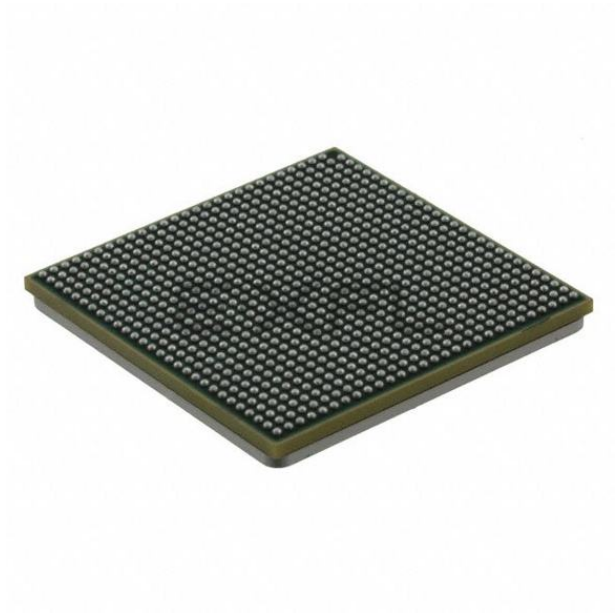

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	-
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (1)
USB	USB 2.0 (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 90°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8535avtaqga

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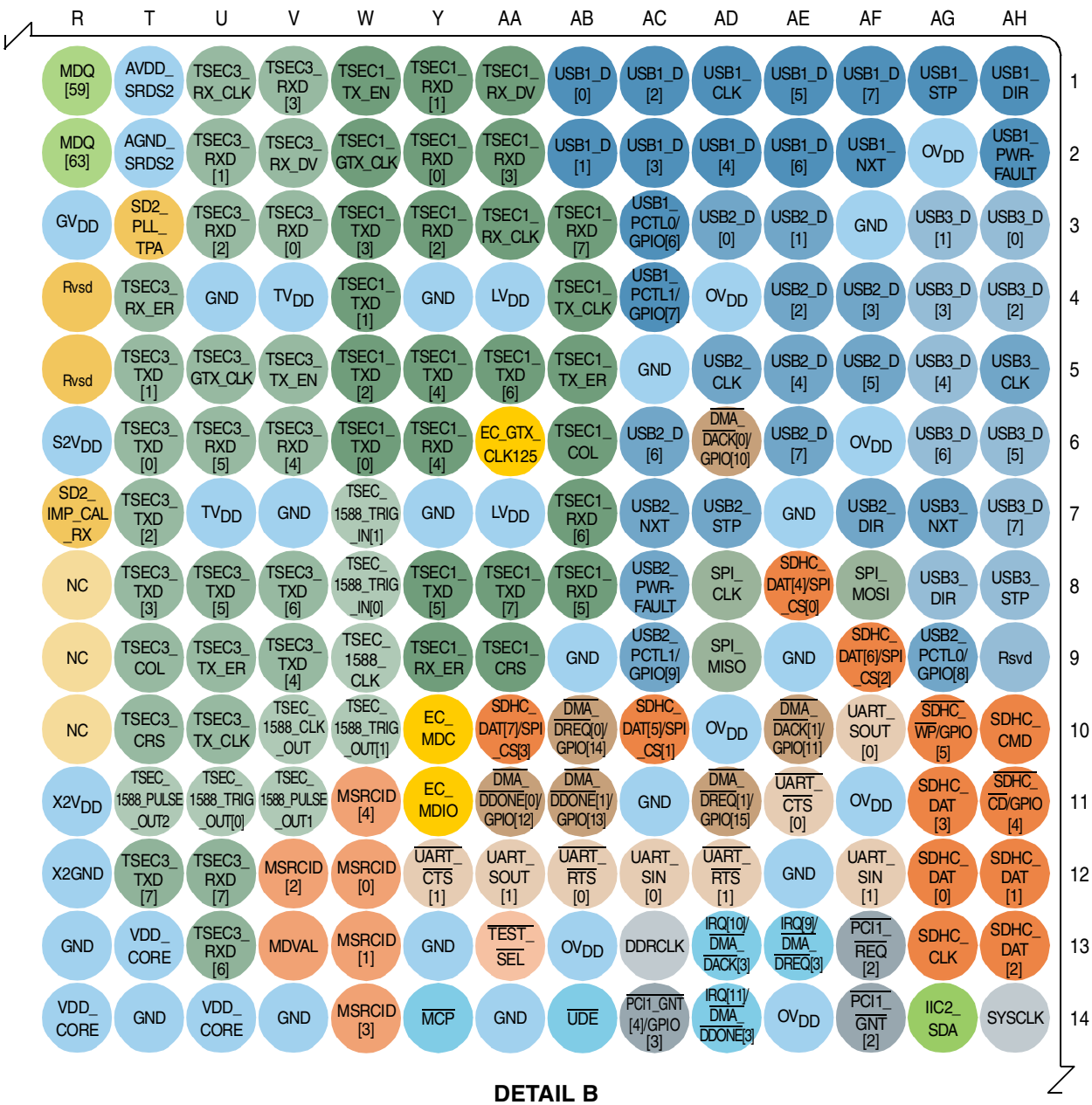


DETAIL B

Figure 4. Chip Pin Map Detail B

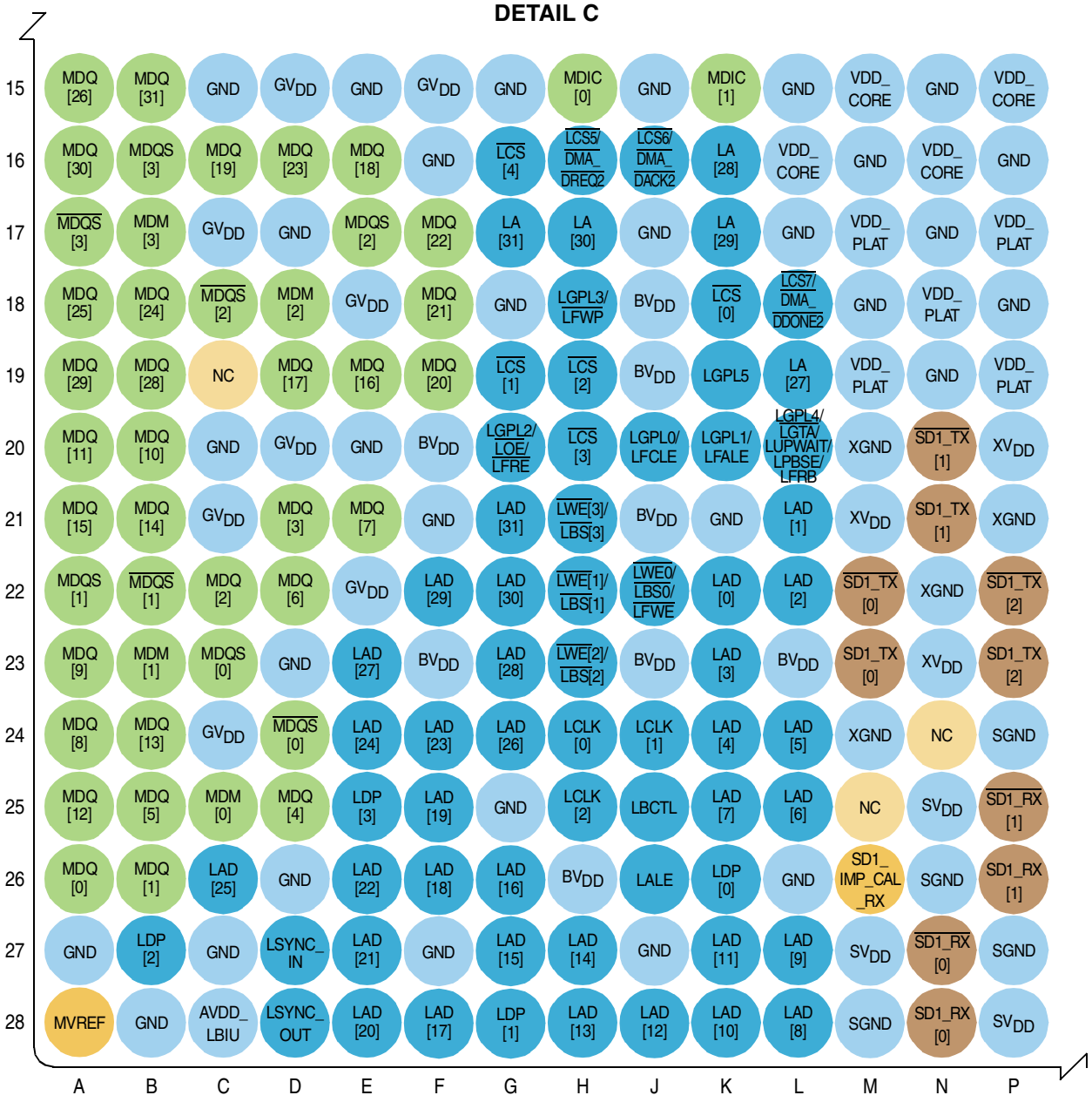


Figure 5. Chip Pin Map Detail C

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
LAD[0:31]	Muxed data / address	K22,L21,L22,K23,K24, L24,L25,K25,L28,L27, K28,K27,J28,H28,H27, G27,G26,F28,F26,F25, E28,E27,E26,F24,E24, C26,G24,E23,G23,F22, G22,G21	I/O	BV_{DD}	5,9,29
LDP[0:3]	Data parity	K26,G28,B27,E25	I/O	BV_{DD}	29
LA[27]	Burst address	L19	O	BV_{DD}	5,9,29
LA[28:31]	Port address	K16,K17,H17,G17	O	BV_{DD}	5,7,9,29
$\overline{\text{LCS}}$[0:4]	Chip selects	K18,G19,H19,H20,G16	O	BV_{DD}	29
$\overline{\text{LCS5}}$/$\overline{\text{DMA\_DREQ2}}$	Chips selects / DMA Request	H16	I/O	BV_{DD}	1,29
$\overline{\text{LCS6}}$/$\overline{\text{DMA\_DACK2}}$	Chips selects / DMA Ack	J16	O	BV_{DD}	1,29
$\overline{\text{LCS7}}$/$\overline{\text{DMA\_DDONE2}}$	Chips selects / DMA Done	L18	O	BV_{DD}	1,29
$\overline{\text{LWE0}}$/$\overline{\text{LBS0}}$/$\overline{\text{LFWE}}$	Write enable / Byte select	J22	O	BV_{DD}	5,9,29
$\overline{\text{LWE[1:3]}}$/$\overline{\text{LBS[1:3]}}$	Write enable / Byte select	H22,H23,H21	O	BV_{DD}	5,9,29
LBCTL	Buffer control	J25	O	BV_{DD}	5,8,9,29
LALE	Address latch enable	J26	O	BV_{DD}	5,8,9,29
LGPL0/LFCLE	UPM general purpose line 0 / FLash command latch enable	J20	O	BV_{DD}	5,9,29
LGPL1/LFALE	UPM general purpose line 1 / Flash address latch enable	K20	O	BV_{DD}	5,9,29
LGPL2/$\overline{\text{LOE}}$/$\overline{\text{LFRE}}$	UPM general purpose line 2 / Output enable/Flash read enable	G20	O	BV_{DD}	5,8,9,29
LGPL3/$\overline{\text{LFWP}}$	UPM general purpose line 3 / Flash write protect	H18	O	BV_{DD}	5,9,29
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT /LPBSE/LFRB	UPM general purpose line 4 / Target Ack/Wait/SDRAM parity byte select/Flash Ready-busy	L20	I/O	BV_{DD}	29, 35
LGPL5	UPM general purpose line 5 / Amux	K19	O	BV_{DD}	5,9,29
LCLK[0:2]	Local bus clock	H24,J24,H25	O	BV_{DD}	29
LSYNC_IN	Synchronization	D27	I	BV_{DD}	29
LSYNC_OUT	Local bus DLL	D28	O	BV_{DD}	29
DMA					
$\overline{\text{DMA\_DACK}}$[0:1] /GPIO[10:11]	DMA Acknowledge	AD6,AE10	O	OV_{DD}	—

Table 3. Recommended Operating Conditions

Characteristic		Symbol	Recommended Value	Unit	Notes
Core supply voltage		V_{DD_CORE}	1.0 ± 50 mV	V	—
Platform supply voltage		V_{DD_PLAT}	1.0 ± 50 mV	V	—
PLL core supply voltage		AV_{DD_CORE}	1.0 ± 50 mV	V	2
PLL other supply voltage		AV_{DD}	1.0 ± 50 mV	V	2
Core power supply for SerDes transceivers		SV_{DD}	1.0 ± 50 mV	V	—
Pad power supply for SerDes transceivers and PCI Express		XV_{DD}	1.0 ± 50 mV	V	—
DDR SDRAM Controller I/O supply voltage	DDR2 SDRAM Interface	GV_{DD}	1.8 V ± 90 mV	V	3
	DDR3 SDRAM Interface		1.5 V ± 75 mV		
Three-speed Ethernet I/O voltage		LV_{DD} (eTSEC1)	3.3 V ± 165 mV 2.5 V ± 125 mV	V	5
		TV_{DD} (eTSEC3)	3.3 V ± 165 mV 2.5 V ± 125 mV		
PCI, DUART, system control and power management, I^2C, USB, eSDHC, eSPI and JTAG I/O voltage, MII management voltage		OV_{DD}	3.3 V ± 165 mV	V	4
Local bus I/O voltage		BV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Input voltage	DDR2 and DDR3 SDRAM Interface signals	MV_{IN}	GND to GV_{DD}	V	3
	DDR2 and DDR3 SDRAM Interface reference	MV_{REF}	$GV_{DD}/2$ ± 1%	V	—
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to LV_{DD} GND to TV_{DD}	V	5
	Local bus signals	BV_{IN}	GND to BV_{DD}	V	—
	PCI, Local bus, DUART, SYSCLK, system control and power management, I^2C, and JTAG signals	OV_{IN}	GND to OV_{DD}	V	4
Operating Temperature range	Commercial	T_A T_J	T_A= 0 (min) to T_J= 90(max)	°C	6
	Industrial standard temperature range		T_A= 0 (min) to T_J= 105 (max)		
	Extended temperature range		T_A= -40 (min) to T_J= 105 (max)		

Notes:

2. This voltage is the input to the filter discussed in Section 3.2.1, "PLL Power Supply Filtering," and not necessarily the voltage at the AVDD pin, which may be reduced from VDD by the filter.
3. **Caution**: MVIN must not exceed GVDD by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution**: OVIN must not exceed OVDD by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
5. **Caution**: L/TVIN must not exceed L/TVDD by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
6. Minimum temperature is specified with T_A; maximum temperature is specified with T_J.

2.4.4 eTSEC Gigabit Reference Clock Timing

This table provides the eTSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications for the chip.

Table 8. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
EC_GTX_CLK rise and fall time LV_{DD}, TV_{DD} = 2.5V LV_{DD}, TV_{DD} = 3.3V	t_{G125R}/t_{G125F}	—	—	 0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2

Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5V and 2.0V for L/TVDD=2.5V, and from 0.6 and 2.7V for L/TVDD=3.3V at 0.6 V and 2.7 V.
2. EC_GTX_CLK125 is used to generate the GTX clock for the eTSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47/53% as long as the PHY device can tolerate the duty cycle generated by the eTSEC GTX_CLK. See Section 2.9.2.6, "RGMII and RTBI AC Timing Specifications," for duty cycle for 10Base-T and 100Base-T reference clock.

2.4.5 DDR Clock Timing

This table provides the DDR clock (DDRCLK) AC timing specifications for the chip.

Table 9. DDRCLK AC Timing Specifications

At recommended operating conditions with OV_{DD} of 3.3V ± 5%.

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
DDRCLK frequency	f_{DDRCLK}	66	—	166	MHz	1
DDRCLK cycle time	t_{DDRCLK}	6.0	—	15.15	ns	—
DDRCLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	1.2	ns	2
DDRCLK duty cycle	t_{KHK}/t_{DDRCLK}	40	—	60	%	—
DDRCLK jitter	—	—	—	+/– 150	ps	3, 4

Notes:

1. **Caution:** The DDR complex clock to DDRCLK ratio settings must be chosen such that the resulting DDR complex clock frequency does not exceed the maximum or minimum operating frequencies. See Section 2.23.4, "DDR/DDRCLK PLL Ratio," for ratio settings.
2. Rise and fall times for DDRCLK are measured at 0.6 V and 2.7 V.
3. The DDRCLK driver's closed loop jitter bandwidth should be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track DDRCLK drivers with the specified jitter.
4. For spread spectrum clocking, guidelines are +0% to –1% down spread at a modulation rate between 20 kHz and 60 kHz on DDRCLK.

2.4.6 Platform to FIFO Restrictions

Please note the following FIFO maximum speed restrictions based on platform speed. The “platform clock (CCB) frequency” in the following formula refers to the maximum platform (CCB) frequency of the speed bins the part belongs to, which is defined in Table 73.

For FIFO GMII mode:

FIFO TX/RX clock frequency <= platform clock frequency/3.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 167 MHz

For FIFO encoded mode:

FIFO TX/RX clock frequency <= platform clock frequency/3.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 167 MHz

2.4.7 Other Input Clocks

For information on the input clocks of other functional blocks of the platform such as SerDes, and eTSEC, see the specific section of this document.

2.5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the chip. This table provides the RESET initialization AC timing specifications for the DDR SDRAM component(s).

Table 10. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	100	—	µs	—
Minimum assertion time for $\overline{\text{SRESET}}$	3	—	Sysclk	1
PLL input setup time with stable SYSCLK before $\overline{\text{HRESET}}$ negation	100	—	µs	—
Input setup time for POR configurations (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for all POR configurations (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configurations with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1
$\overline{\text{HRESET}}$ rise time	—	1	SYSCLK	—

Notes:

1. SYSCLK is the primary clock input for the chip.

This table provides the PLL lock times.

Table 11. PLL Lock Times

Parameter/Condition	Min	Max	Unit	Notes
PLL lock times	—	100	µs	—
Local bus PLL	—	50	µs	—
PCI bus lock time	—	50	µs	—

2.6 DDR2 and DDR3 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the chip. Note that DDR2 SDRAM is GV_{DD}(type) = 1.8 V and DDR3 SDRAM is GV_{DD}(type) = 1.5 V.

2.6.1 DDR2 and DDR3 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR SDRAM component(s) of the chip when interfacing to DDR2 SDRAM.

Table 12. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.7	1.9	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF}+ 0.125	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.125	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the chip. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

This table provides the recommended operating conditions for the DDR SDRAM controller of the chip when interfacing to DDR3 SDRAM.

Table 13. DDR3 SDRAM Interface DC Electrical Characteristics for GV_{DD}(typ) = 1.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.425	1.575	V	1
I/O reference voltage	$MV_{REF}n$	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
Input high voltage	V_{IH}	$MV_{REF}n$ + 0.100	GV_{DD}	V	—
Input low voltage	V_{IL}	GND	$MV_{REF}n$ – 0.100	V	—
Output leakage current	I_{OZ}	–50	50	μA	3

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. $MV_{REF}n$ is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MV_{REF}n$ may not exceed ±1% of the DC value.
3. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 17. DDR3 SDRAM Input AC Timing Specifications for 1.5-V Interface

At recommended operating conditions with GV_{DD} of 1.5 V ± 5%. DDR3 data rate is between 606MHz and 667MHz.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.175	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.175	—	V	—

Table 18. DDR2 and DDR3 SDRAM Interface Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8 V ± 5% for DDR2 or 1.5 V ± 5% for DDR3.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC	t_{CISKEW}	—	—	ps	1, 2
667 MHz	—	–240	240	—	3
533 MHz	—	–300	300	—	—
400 MHz	—	–365	365	—	—

Note:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: t_{DISKEW} =+/-(T/4 - abs(t_{CISKEW})) where T is the clock period and abs(t_{CISKEW}) is the absolute value of t_{CISKEW}.
3. Maximum DDR2 and DDR3 frequency is 667MHz.

This figure shows the DDR2 and DDR3 SDRAM interface input timing diagram.

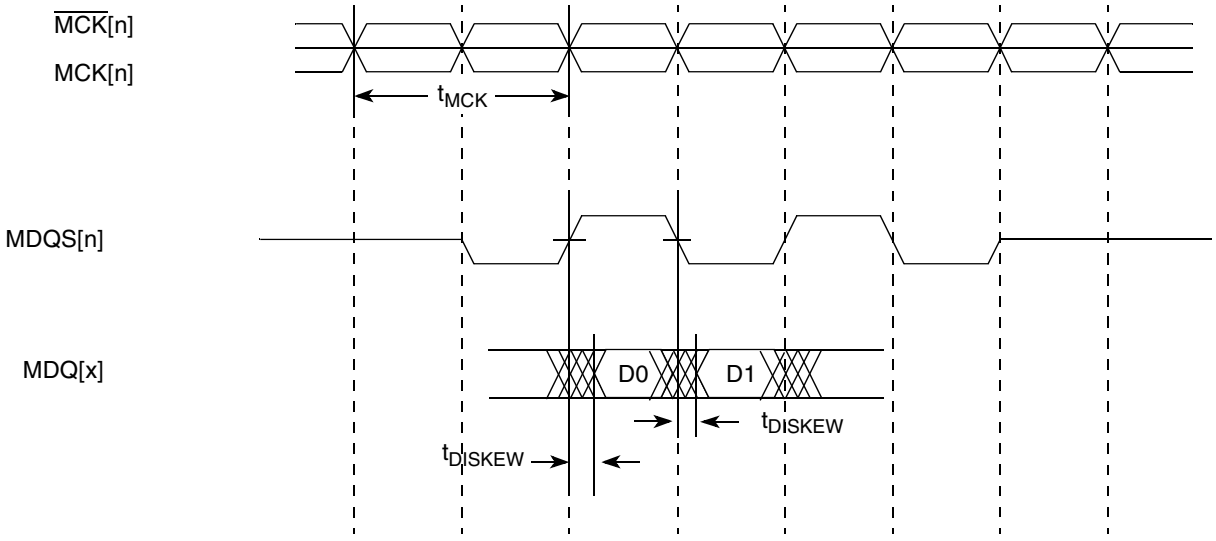


Figure 8. DDR SDRAM Input Timing Diagram

2.8 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the chip.

2.8.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface.

Table 22. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	– 0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

2.8.2 DUART AC Electrical Specifications

This table provides the AC timing parameters for the DUART interface.

Table 23. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	CCB clock/1,048,576	baud	2
Maximum baud rate	CCB clock/16	baud	2,3
Oversample rate	16	—	4

Notes:

2. CCB clock refers to the platform clock.
3. Actual attainable baud rate will be limited by the latency of interrupt processing.
4. The middle of a start bit is detected as the 8^{th} sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16^{th} sample.

2.9 Ethernet: Enhanced Three-Speed Ethernet (eTSEC), MII Management

This section provides the AC and DC electrical characteristics for enhanced three-speed and MII management.

This figure shows the TBI receive AC timing diagram.

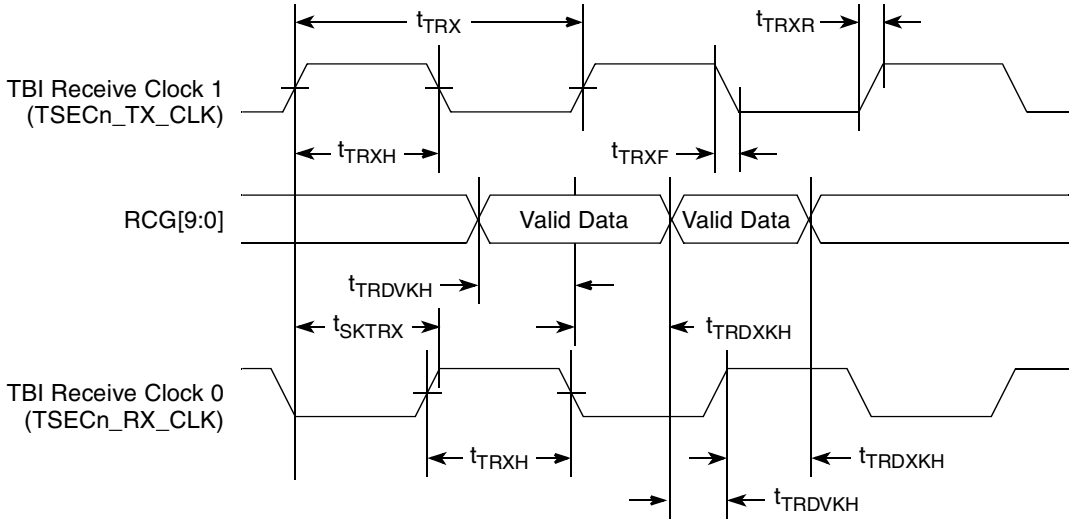


Figure 23. TBI Receive AC Timing Diagram

2.9.2.5 TBI Single-Clock Mode AC Specifications

When the eTSEC is configured for TBI modes, all clocks are supplied from external sources to the relevant eTSEC interface. In single-clock TBI mode, when a 125-MHz TBI receive clock is supplied on TSEC*n* pin (no receive clock is used on in this mode, whereas for the dual-clock mode this is the PMA0 receive clock). The 125-MHz transmit clock is applied on the in all TBI modes.

A summary of the single-clock TBI mode AC specifications for receive appears in the following table.

Table 34. TBI single-clock Mode Receive AC Timing Specification

At recommended operating conditions with LV_{DD}/TV_{DD} of 3.3 V ± 5%

Parameter/Condition	Symbol	Min	Typ	Max	Unit
RX_CLK clock period	t_{TRR}	7.5	8.0	8.5	ns
RX_CLK duty cycle	t_{TRRH}	40	50	60	%
RX_CLK peak-to-peak jitter	t_{TRRJ}	—	—	250	ps
Rise time RX_CLK (20%–80%)	t_{TRRR}	—	—	1.0	ns
Fall time RX_CLK (80%–20%)	t_{TRRF}	—	—	1.0	ns
RCG[9:0] setup time to RX_CLK rising edge	t_{TRRDV}	2.0	—	—	ns
RCG[9:0] hold time to RX_CLK rising edge	t_{TRRDX}	1.0	—	—	ns

Table 51. Local Bus General Timing Parameters (BV_{DD} = 3.3 V DC) (continued)

Parameter	Symbol [1]	Min	Max	Unit	Notes
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is guaranteed with LBCR[AHD] = 0.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.

This table describes the general timing parameters of the local bus interface at BV_{DD} = 2.5 V DC.

Table 52. Local Bus General Timing Parameters (BV_{DD} = 2.5 V DC)

Parameter	Configuration	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	—	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	—	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	—	$t_{LBKSKEW}$	—	150	ps	7
Input setup to local bus clock (except LUPWAIT)	—	$t_{LBIVKH1}$	1.9	—	ns	3, 4
LUPWAIT input setup to local bus clock	—	$t_{LBIVKH2}$	1.8	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	—	$t_{LBIXKH1}$	1.1	—	ns	3, 4
LUPWAIT input hold from local bus clock	—	$t_{LBIXKH2}$	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	—	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	—	$t_{LBKHOV1}$	—	2.4	ns	—
Local bus clock to data valid for LAD/LDP	—	$t_{LBKHOV2}$	—	2.5	ns	3
Local bus clock to address valid for LAD	—	$t_{LBKHOV3}$	—	2.4	ns	3
Local bus clock to LALE assertion	—	$t_{LBKHOV4}$	—	2.4	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	—	$t_{LBKHOX1}$	0.8	—	ns	3

Table 52. Local Bus General Timing Parameters (BV_{DD} = 2.5 V DC) (continued)

Parameter	Configuration	Symbol [1]	Min	Max	Unit	Notes
Output hold from local bus clock for LAD/LDP	—	$t_{LBKHOX2}$	0.8	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	—	$t_{LBKHOZ1}$	—	2.6	ns	5
Local bus clock to output high impedance for LAD/LDP	—	$t_{LBKHOZ2}$	—	2.6	ns	5

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 2.5-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is guaranteed with LBCR[AHD] = 0.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.

This table describes the general timing parameters of the local bus interface at BV_{DD} = 1.8 V DC.

Table 53. Local Bus General Timing Parameters (BV_{DD} = 1.8 V DC)

Parameter	Configuration	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	—	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	—	t_{LBKH}/t_{LBK}	43	57	%	
LCLK[n] skew to LCLK[m] or LSYNC_OUT	—	$t_{LBKSKEW}$		150	ps	7
Input setup to local bus clock (except LUPWAIT)	—	$t_{LBIVKH1}$	2.4	—	ns	3, 4
LUPWAIT input setup to local bus clock	—	$t_{LBIVKH2}$	1.9	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	—	$t_{LBIXKH1}$	1.1	—	ns	3, 4
LUPWAIT input hold from local bus clock	—	$t_{LBIXKH2}$	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	—	t_{LBOTOT}	1.2	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	—	$t_{LBKHOV1}$	—	3.2	ns	—
Local bus clock to data valid for LAD/LDP	—	$t_{LBKHOV2}$	—	3.2	ns	3
Local bus clock to address valid for LAD	—	$t_{LBKHOV3}$	—	3.2	ns	3
Local bus clock to LALE assertion	—	$t_{LBKHOV4}$	—	3.2	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	—	$t_{LBKHOX1}$	0.9	—	ns	3

Table 54. Local Bus General Timing Parameters—PLL Bypassed (continued)

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to data valid for LAD/LDP	$t_{LBKLOV2}$	—	0.5	ns	4
Local bus clock to address valid for LAD, and LALE	$t_{LBKLOV3}$	—	0.5	ns	4
Local bus clock to LALE assertion	$t_{LBKLOV4}$	—	0.5	ns	4
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKLOX1}$	—	2.2	ns	4,8
Output hold from local bus clock for LAD/LDP	$t_{LBKLOX2}$	—	2.2	ns	4,8
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKLOZ1}$	—	0.1	ns	7
Local bus clock to output high impedance for LAD/LDP	$t_{LBKLOZ2}$	—	0.1	ns	7

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to local bus clock for PLL bypass mode.
3. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.
4. All signals are measured from BVDD/2 of the rising edge of local bus clock for PLL bypass mode to 0.4 x BVDD of the signal in question for 3.3-V signaling levels.
5. Input timings are measured at the pin.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is guaranteed with LBCR[AHD] = 0.
7. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
8. These timing parameters for PLL bypass mode are defined in the opposite direction of the PLL enabled output hold timing parameters.

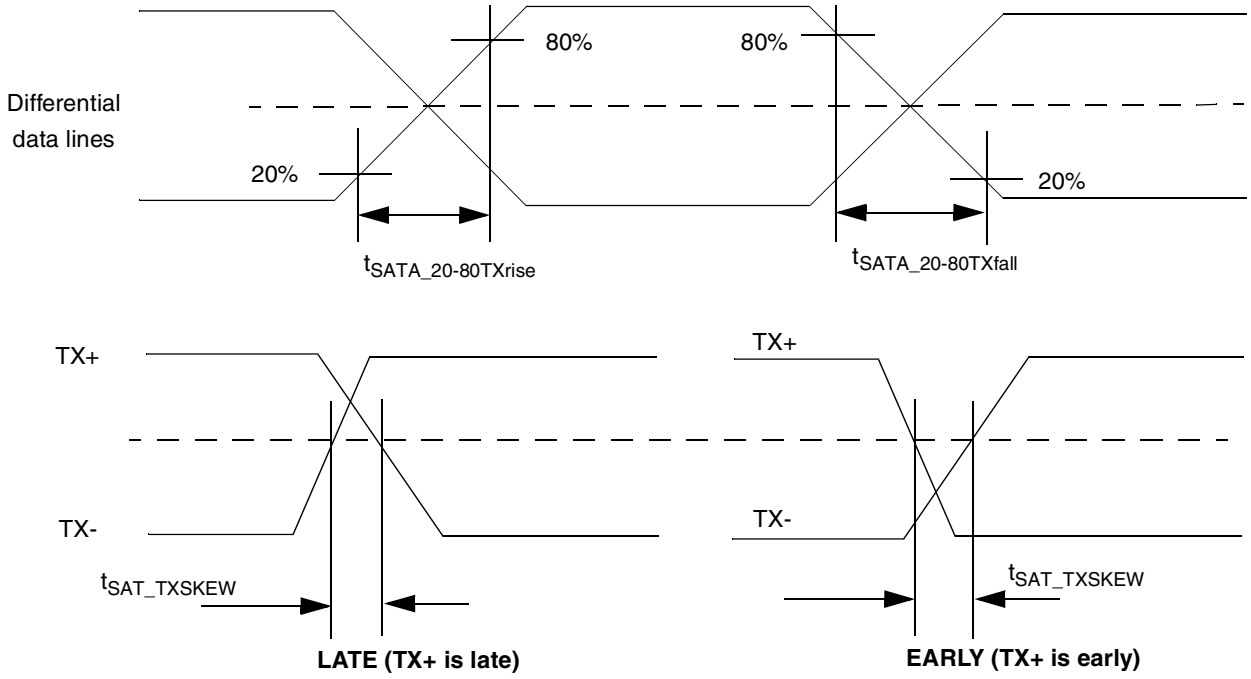


Figure 50. Signal Rise and Fall Times and Differential Skew

2.16.3 Differential Receiver (RX) Input Characteristics

This table provides the differential receiver (RX) input characteristics for the SATA interface.

Table 61. Differential Receiver (RX) Input Characteristics

Parameter	Symbol	Min	Typical	Max	Units	Notes
RX Differential Input Voltage 1.5G 3.0G	V_{SATA_RXDIFF}	 240 240	 400 —	 600 750	mVp-p	1
RX rise/fall time 1.5G 3.0G	$t_{SATA\_20\text{-}80RX}$	100 67	— —	273 136	ps	—
RX Differential skew 1.5G 3.0G	t_{SATA_RXSKEW}	— —	— —	— 50	ps	—
RX Differential pair impedance 1.5G	$Z_{SATA\_RXDIFFIM}$	85	—	115	ohm	—
RX Single-Ended impedance 1.5G	Z_{SATA_RXSEIM}	40	—	—	ohm	—
DC Coupled Common Mode Voltage	V_{dc_cm}	200	250	450	mV	5

Table 61. Differential Receiver (RX) Input Characteristics (continued)

Parameter	Symbol	Min	Typical	Max	Units	Notes
RX Differential Mode Return loss 150 MHz - 300 MHz 300 MHz - 600 MHz 600 MHz - 1.2 GHz 1.2 GHz - 2.4 GHz 2.4 GHz - 3.0 GHz 3.0 GHz - 5.0 GHz	RL_{SATA_RXDD11}	 — — — — — —	 — — — — — —	 18 14 10 8 3 1	 dB	2, 3
RX Common Mode Return loss 150 MHz - 300 MHz 300 MHz - 600 MHz 600 MHz - 1.2 GHz 1.2 GHz - 2.4 GHz 2.4 GHz - 3.0 GHz 3.0 GHz - 5.0 GHz	RL_{SATA_RXCC11}	 — — — — — —	 — — — — — —	 5 5 2 2 2 1	 dB	2, 3, 4
RX Impedance Balance 150 MHz - 300 MHz 300 MHz - 600 MHz 600 MHz - 1.2 GHz 1.2 GHz - 2.4 GHz 2.4 GHz - 3.0 GHz 3.0 GHz - 5.0 GHz	RL_{SATA_RXDC11}	 — — — — — —	 — — — — — —	 30 30 20 10 4 4	 dB	2, 3
Deterministic jitter 1.5G 3.0G	U_{SATA_RXDJ}	—	—	 0.4 0.47	 UI	—
Total Jitter 1.5G 3.0G	U_{SATA_RXTJ}	—	—	 0.65 0.65	 UI	—

Notes:
1. The min values apply only to Gen1m, and Gen2m. the min values for Gen1i is 325 mVp-p and for Gen2i is 275 mVp-p.
2. Only applies when operating in 3.0Gb data rate mode.
3. The max value stated for 3.0 GHz - 5.0 GHz range only applies to Gen2i mode and not to Gen2m mode.
4. The max value stated for 2.4 GHz - 3.0 GHz range only applies to Gen2i mode for Gen2m the value is 1.
5. Only applies to Gen1i mode.

Table 72. Differential Receiver (RX) Input Specifications (continued)

Symbol	Parameter	Min	Nom	Max	Units	Comments
$L_{TX-SKEW}$	Total Skew	—	—	20	ns	Skew across all lanes on a Link. This includes variation in the length of SKP ordered set (for example, COM and one to five Symbols) at the RX as well as any delay differences arising from the interconnect itself.

Notes:
1. No test load is necessarily associated with this value.
2. Specified at the measurement point and measured over any 250 consecutive UIs. The test load in Figure 71 should be used as the RX device when taking measurements (also refer to the Receiver compliance eye diagram shown in Figure 70). If the clocks to the RX and TX are not derived from the same reference clock, the TX UI recovered from 3500 consecutive UI must be used as a reference for the eye diagram.
3. A T_{RX-EYE} = 0.40 UI provides for a total sum of 0.60 UI deterministic and random jitter budget for the Transmitter and interconnect collected any 250 consecutive UIs. The $T_{RX-EYE-MEDIAN-to-MAX-JITTER}$ specification ensures a jitter distribution in which the median and the maximum deviation from the median is less than half of the total. UI jitter budget collected over any 250 consecutive TX UIs. It should be noted that the median is not the same as the mean. The jitter median describes the point in time where the number of jitter points on either side is approximately equal as opposed to the averaged time value. If the clocks to the RX and TX are not derived from the same reference clock, the TX UI recovered from 3500 consecutive UI must be used as the reference for the eye diagram.
4. The Receiver input impedance shall result in a differential return loss greater than or equal to 15 dB with the D+ line biased to 300 mV and the D- line biased to -300 mV and a common mode return loss greater than or equal to 6 dB (no bias required) over a frequency range of 50 MHz to 1.25 GHz. This input impedance requirement applies to all valid input levels. The reference impedance for return loss measurements for is 50 ohms to ground for both the D+ and D- line (that is, as measured by a Vector Network Analyzer with 50 ohm probes - see Figure 71). Note: that the series capacitors CTX is optional for the return loss measurement.
5. Impedance during all LTSSM states. When transitioning from a Fundamental Reset to Detect (the initial state of the LTSSM) there is a 5 ms transition time before Receiver termination values must be met on all un-configured Lanes of a Port.
6. The RX DC Common Mode Impedance that exists when no power is present or Fundamental Reset is asserted. This helps ensure that the Receiver Detect circuit will not falsely assume a Receiver is powered on when it is not. This term must be measured at 300 mV above the RX ground.
7. It is recommended that the recovered TX UI is calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function. Least squares and median deviation fits have worked well with experimental and simulated data.

2.22 Receiver Compliance Eye Diagrams

The RX eye diagram in Figure 70 is specified using the passive compliance/test measurement load (see Figure 71) in place of any real PCI Express RX component.

Note: In general, the minimum Receiver eye diagram measured with the compliance/test measurement load (see Figure 71) will be larger than the minimum Receiver eye diagram measured over a range of systems at the input Receiver of any real PCI Express component. The degraded eye diagram at the input Receiver is due to traces internal to the package as well as silicon parasitic characteristics which cause the real PCI Express component to vary in impedance from the compliance/test measurement load. The input Receiver eye diagram is implementation specific and is not specified. RX component designer should provide additional margin to adequately compensate for the degraded minimum Receiver eye diagram (shown in Figure 70) expected at the input Receiver based on some adequate combination of system simulations and the Return Loss measured looking into the RX package and silicon. The RX eye diagram must be aligned in time using the jitter median to locate the center of the eye diagram.

The eye diagram must be valid for any 250 consecutive UIs.

The recommended attachment method to the heat sink is illustrated in the following figure. The heat sink should be attached to the printed-circuit board with the spring force centered over the die. This spring force should not exceed 10 pounds force (45 Newton).

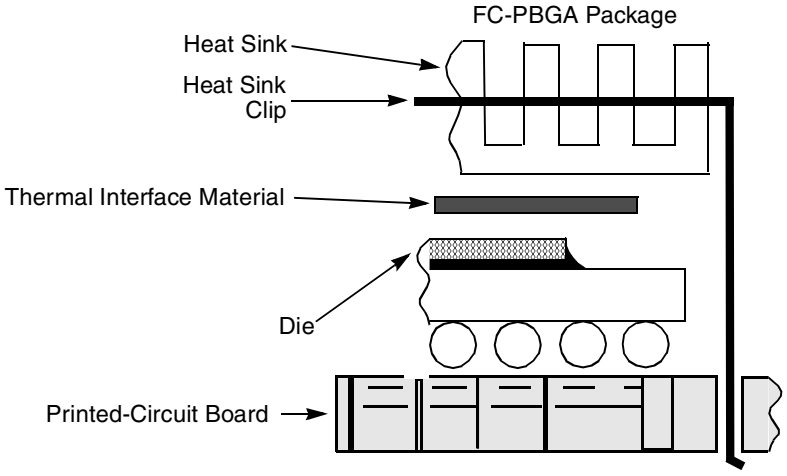


Figure 73. Package Exploded Cross-Sectional View with Several Heat Sink Options

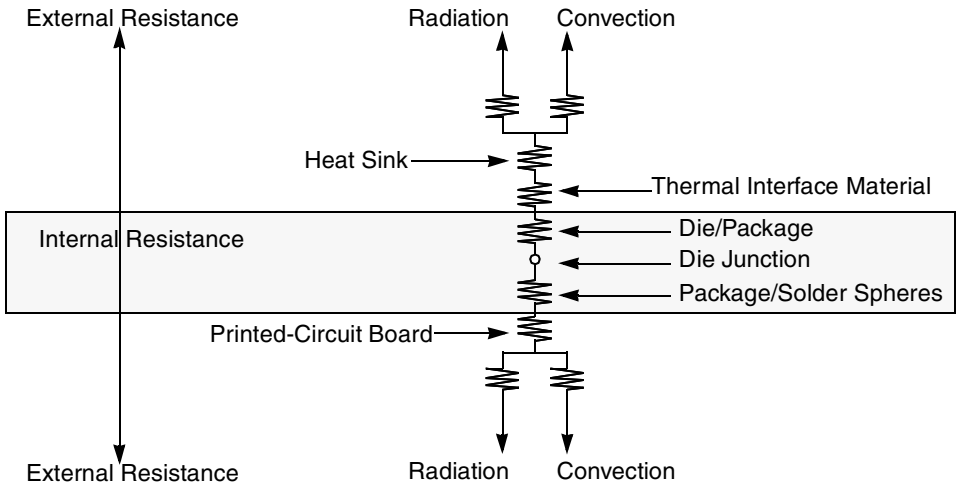
The system board designer can choose between several types of heat sinks to place on the chip. Ultimately, the final selection of an appropriate heat sink depends on many factors, such as thermal performance at a given air velocity, spatial volume, mass, attachment method, assembly, and cost. Several heat sinks offered by Aavid Thermalloy, Advanced Thermal Solutions, Alpha Novatech, IERC, Chip Coolers, Millennium Electronics, and Wakefield Engineering offer different heat sink-to-ambient thermal resistances, that will allow the chip to function in various environments.

2.24.3.1 Internal Package Conduction Resistance

For the packaging technology, shown in Table 70, the intrinsic internal conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance
- The die junction-to-board thermal resistance

This figure depicts the primary heat transfer path for a package with an attached heat sink mounted to a printed-circuit board.



(Note the internal versus external package resistance)

Figure 74. Package with Heat Sink Mounted to a Printed-Circuit Board

The heat sink removes most of the heat from the chip for most applications. Heat generated on the active side of the chip is conducted through the silicon and through the heat sink attach material (or thermal interface material), and finally to the heat sink. The junction-to-case thermal resistance is low enough that the heat sink attach material and heat sink thermal resistance are the dominant terms.

2.24.3.2 Thermal Interface Materials

A thermal interface material is required at the package-to-heat sink interface to minimize the thermal contact resistance. The performance of thermal interface materials improves with increased contact pressure. This performance characteristic chart is generally provided by the thermal interface vendors.

3 Hardware Design Considerations

This section provides electrical and thermal design recommendations for successful application of the chip.

3.1 System Clocking

This chip includes seven PLLs:

- The platform PLL generates the platform clock from the externally supplied SYSCLK input. The frequency ratio between the platform and SYSCLK is selected using the platform PLL ratio configuration bits as described in Section 2.23.2, “CCB/SYSCLK PLL Ratio.”
- The e500 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e500 core clock and the platform clock is selected using the e500 PLL ratio configuration bits as described in Section 2.23.3, “e500 Core PLL Ratio.”
- The PCI PLL generates the clocking for the PCI bus
- The local bus PLL generates the clock for the local bus.
- There is a PLL for the SerDes1 block to be used for PCI Express interface
- There is a PLL for the SerDes2 block to be used for SGMII and SATA interfaces.
- The DDR PLL generates the DDR clock from the externally supplied DDRCLK input in asynchronous mode. The frequency ratio between the DDR clock and DDRCLK is described in Section 2.23.4, “DDR/DDRCLK PLL Ratio.”

3.2 Power Supply Design and Sequencing

3.2.1 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins (AV_{DD}_PLAT, AV_{DD}_CORE, AV_{DD}_PCI, AV_{DD}_LBIU, and AV_{DD}_SRDS respectively). The AV_{DD} level should always be equivalent to V_{DD}, and preferably these voltages will be derived directly from V_{DD} through a low frequency filter scheme such as the following.

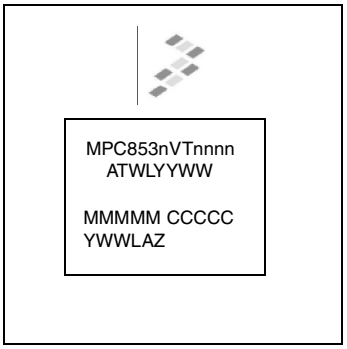
There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide independent filter circuits per PLL power supply as illustrated in Figure 75, one to each of the AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum Effective Series Inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV_{DD} pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of 783 FC-PBGA the footprint, without the inductance of vias.

4.2 Part Marking

Parts are marked as in the example shown in the following figure.



FC-PBGA

Notes:

MMMMM is the 5-digit mask number.
ATWLYYWW is the traceability code.
CCCCC is the country of assembly. This space is left blank if parts are assembled in the United States.

Figure 80. Part Marking for FC-PBGA

4.3 Part Numbering

These tables list all part numbers that are offered for the chip.

Table 83. MPC8535 Part Numbers Commercial Tier

Core/Platform/ DDR (MHz)	Standard Temp Without Security	Standard Temp With Security	Notes
600/400/400	MPC8535AVTAKG(A)	MPC8535EAVTAKG(A)	—
800/400/400	MPC8535AVTANG(A)	MPC8535EAVTANG(A)	—
1000/400/400	MPC8535AVTAQG(A)	MPC8535EAVTAQG(A)	—
1250/500/500	MPC8535AVTATH(A)	MPC8535EAVTATH(A)	—
1250/500/667	MPC8535AVTATLA	MPC8535EAVTATLA	—

Table 84. MPC8535 Part Numbers Industrial Tier

Core/Platform/ DDR (MHz)	Standard Temp Without Security	Standard Temp With Security	Extended Temp Without Security	Extended Temp With Security	Notes
600/400/400	MPC8535BVTAKG(A)	MPC8535EBVTAKG(A)	MPC8535CVTAKG(A)	MPC8535ECVTAKG(A)	1
800/400/400	MPC8535BVTANG(A)	MPC8535EBVTANG(A)	MPC8535CVTANG(A)	MPC8535ECVTANG(A)	
1000/400/400	MPC8535BVTAQG(A)	MPC8535EBVTAQG(A)	MPC8535CVTAQG(A)	MPC8535ECVTAQG(A)	
1250/500/500	MPC8535BVTATH(A)	MPC8535EBVTATH(A)	MPC8535CVTATH(A)	MPC8535ECVTATH(A)	
1250/500/667	MPC8535BVTATLA	MPC8535EBVTATLA	MPC8535CVTATLA	MPC8535ECVTATLA	

Note:

1. The last letter A indicates a Rev 1.2 silicon. It would be Rev 1.0 or Rev 1.1 silicon without a letter A